



1. Description

SS039N08NS, the N-channel Enhanced Power MOSFETs, is obtained by advanced double trench technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. This is suitable device for DC-DC and high speed switching applications.

KEY CHARACTERISTICS

Parameter	Value	Unit
V_{DS}	80	V
I_D	110	A
$R_{DS(on).typ}$	3.6	mΩ

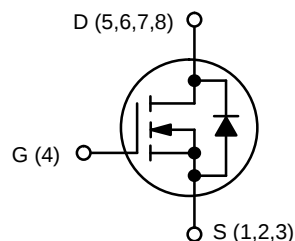
FEATURES

- Fast Switching
- Low On-Resistance ($R_{DS(on)} \leq 3.9m\Omega$)
- Low Gate Charge
- Low Reverse transfer capacitances
- High avalanche ruggedness
- RoHS product

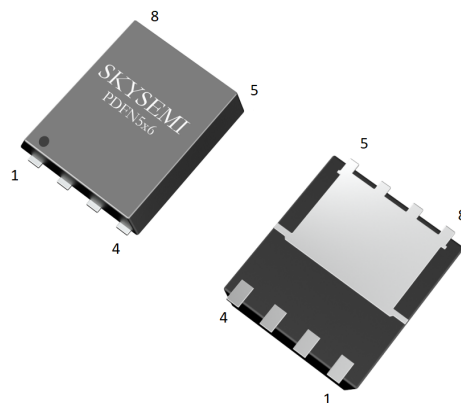
APPLICATIONS

- Switching applications
- DC-DC Converters
- BMS

Schematic Diagram



PDFN5×6



ORDERING INFORMATION

Ordering Code	Package	Product Code	Packing	Quantity
SS039N08NS	PDFN5×6	SS039N08NS	Reel	5000